

## AMENDMENT

### Claim Amendments

1. (canceled)
2. (canceled)
3. (canceled)
4. (canceled)
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)
9. (canceled)
10. (currently amended) A method of forming a continuous isolation region of controlled doping level in a substrate below an active region of a snapback device, comprising using forming a perforated mask with multiple perforations over a silicon substrate,  
implanting dopant through the mask to define multiple spotted implants in the substrate, and  
annealing the device to cause the multiple spotted implants to form the continuous isolation region, wherein the relative size and separation of the perforations in the mask is controlled to control the dopant density of the isolation region during doping of the isolation region.
11. (canceled)
12. (original) A method of claim 10, further comprising exposing the device to one or more predefined elevated temperatures for predefined times.

13. (currently amended) A method of controlling ~~increasing~~ the breakdown voltage of a snapback device comprising  
forming an isolation layer in a substrate of said snapback device, and  
thereafter forming an active region above the isolation layer, wherein forming the isolation layer includes forming spotted implants in the substrate and annealing the device to cause ~~causing~~ the spotted implants substantially to combine to form said isolation region, the size and separation of the spotted implants is chosen to provide an isolation region of desired doping density.
14. (original) A method of claim 13, wherein the spotted implants are formed by making use of a mask with intermittent openings.
15. (original) A method of claim 13, wherein the spotted implants are provided before one or both of an epitaxial layer being grown and high diffusion drive taking place.
16. (original) A method of claim 13, wherein the snapback device is an ESD protection device.
17. (canceled)
18. (original) A method of claim 13, further comprising exposing the device to one or more predefined elevated temperatures for predefined times.